

# WSD60P06DN56

P-Ch MOSFET

### **General Description**

The WSD60P06DN56 is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSD60P06DN56 meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

#### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline

**Absolute Maximum Ratings** 

- 100% EAS Guaranteed
- Green Device Available

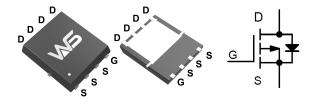
### **Product Summery**

BVDSS	RDSON	ID
-60V	20mΩ	-60A

#### Applications

- Power Management
- Load Switch

#### DFN5X6\_8L Pin Configuration



Symbol	Parameter	Rating	Units	
V <sub>DS</sub>	Drain-Source Voltage	-60	V	
V <sub>GS</sub>	Gate-Source Voltage	±20	V	
I₀@T₀=25℃	Continuous Drain Current, -V <sub>GS</sub> @ -10V -60		А	
I <sub>D</sub> @T <sub>C</sub> =100℃	Continuous Drain Current, -V <sub>GS</sub> @ -10V	-31	A	
I <sub>DM</sub>	Pulsed Drain Current -140		A	
P₀@T₀=25℃	Total Power Dissipation	56	W	
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	

#### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit	
R <sub>eJA</sub>	Thermal Resistance Junction-Ambient		62.5	°C/W	
R <sub>θJC</sub>	Thermal Resistance Junction-Case		2.2	°C/W	



**P-Ch MOSFET** 

### P-Channel Electrical Characteristics (T<sub>J</sub>=25 $^{\circ}$ C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-60			V
В	Ctatia Drain Course On Desister	V <sub>GS</sub> =-10V , I <sub>D</sub> =-18A		20	25	mΩ
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-12A		23	30	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.0	-1.85	-2.5	V
I <sub>DSS</sub>	Drain-Source Leakage Current	$V_{\text{DS}}\text{=-32V}$ , $V_{\text{GS}}\text{=}0\text{V}$ , $T_{\text{J}}\text{=}25^\circ\!\mathrm{C}$			1	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm 20V$ , $V_{DS}=0V$			±100	nA
Qg	Total Gate Charge			72		nC
Q <sub>gs</sub>	Gate-Source Charge			11		
Q <sub>gd</sub>	Gate-Drain Charge			16		
T <sub>d(on)</sub>	Turn-On Delay Time			12		
Tr	Rise Time	VDD = -30 V, RL = 30Ω ID =-1 A, VGEN = -10 V, Rg = 6Ω		10		20
T <sub>d(off)</sub>	Turn-Off Delay Time			125		ns .
T <sub>f</sub>	Fall Time			45		
C <sub>iss</sub>	Input Capacitance	Vbs=-30V,Vgs=0V, f=1.0MHz		3300		
Coss	Output Capacitance			265		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			125		

### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	T <sub>C</sub> =25 <sup>°</sup> C			-20	А
V <sub>SD</sub>	Diode Forward Voltage	$V_{GS}$ =0V , $I_{S}$ =-1A , $T_{J}$ =25 $^{\circ}$ C			-1.2	V

A: The value of R  $_{0.14}$  is measured with the device mounted on  $1in^2$  FR-4 board with 2oz. Copper, in a still air environment with TA=25C. The value in any given

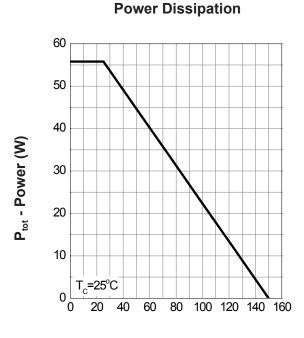
application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

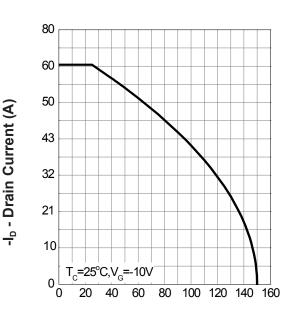
C: The current rating is based on the t≤ 10s junction to ambient thermal resistance rating.



## **Typical Operating Characteristics**

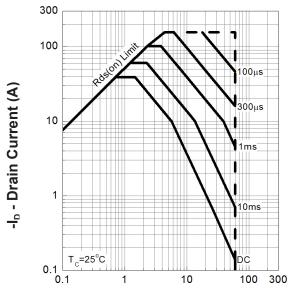


T<sub>j</sub> - Junction Temperature (°C)



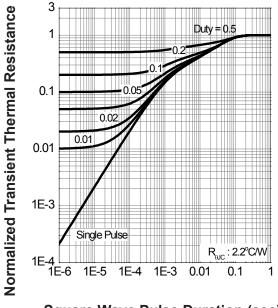
T<sub>i</sub> - Junction Temperature (°C)

Safe Operation Area



-V<sub>DS</sub> - Drain - Source Voltage (V)

**Thermal Transient Impedance** 



Square Wave Pulse Duration (sec)

Drain Current

**WSD60P06DN56** 

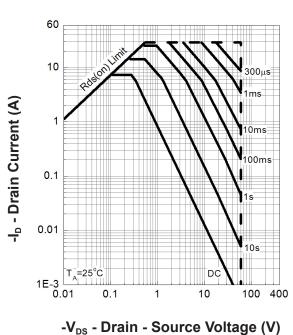
**P-Ch MOSFET** 



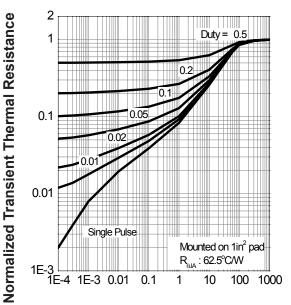
# WSD60P06DN56

P-Ch MOSFET

## **Typical Operating Characteristics**



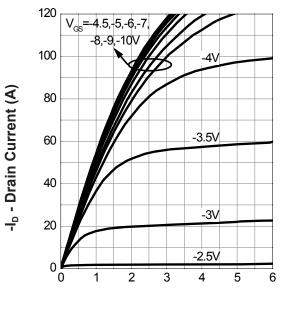
Safe Operation Area



**Thermal Transient Impedance** 

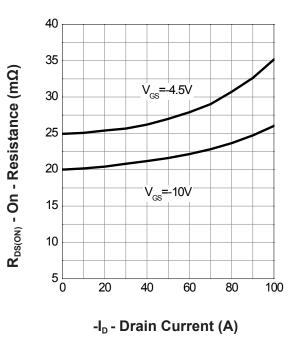
Square Wave Pulse Duration (sec)

**Output Characteristics** 



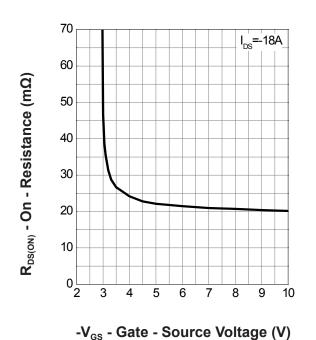
-V<sub>DS</sub> - Drain - Source Voltage (V)

**Drain-Source On Resistance** 





## **Typical Operating Characteristics**

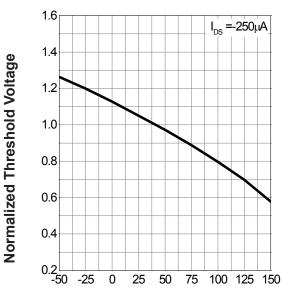


### **Gate-Source On Resistance**



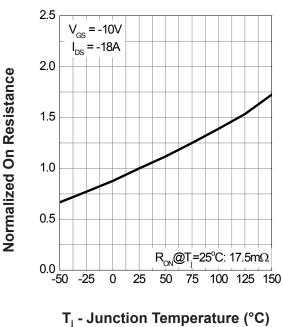
**WSD60P06DN56** 

**P-Ch MOSFET** 

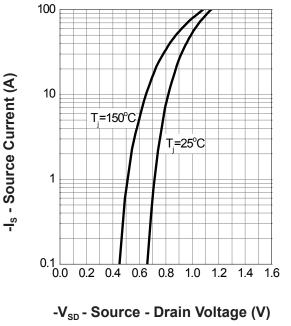


**T**<sub>i</sub> - Junction Temperature (°C)

**Drain-Source On Resistance** 



Source-Drain Diode Forward



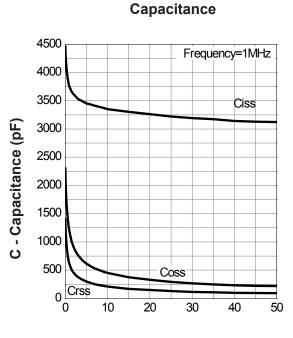
www.winsok.tw



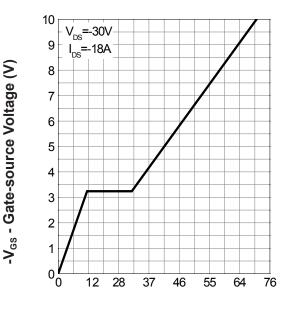
# WSD60P06DN56

**P-Ch MOSFET** 

## **Typical Operating Characteristics**



### -V<sub>DS</sub> - Drain-Source Voltage (V)



**Gate Charge** 

Q<sub>G</sub> - Gate Charge (nC)

() ()  $T_{1}=125^{\circ}C$   $T_{2}=125^{\circ}C$   $T_{2}=125^{\circ}C$  $T_{2$ 

**Transfer Characteristics** 



### Attention

1, Any and all Winsok power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Winsok power representative nearest you before using any Winsok power products described or contained herein in such applications.

2, Winsok power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Winsok power products described or contained herein.

3, Specifications of any and all Winsok power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

4, Winsok power Semiconductor CO., LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

5, In the event that any or all Winsok power products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

6, No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of Winsok power Semiconductor CO., LTD.

7, Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Winsok power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

8, Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the Winsok power product that you Intend to use.

9, this catalog provides information as of Sep.2014. Specifications and information herein are subject to change without notice.